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NTE ELECTRONICS, INC.
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NTE243 (NPN) & NTE244 (PNP)
Silicon Complementary Transistors
Darlington Power Amplifier

Description:

The NTE243 (NPN) and NTE244 (PNP) are silicon complementary Darlington transistors in a TO3 type case designed for general–purpose amplifier and low–frequency switching applications.

Features:

- High DC Current Gain: h_{FE} = 3000 Typ @ I_C = 4A
- Collector–Emitter Sustaining Voltage: $V_{CEO(sus)}$ = 80V Min @ 100mA
- Low Collector–Emitter Saturation Voltage:
  $V_{CE(sat)}$ = 2V Max @ I_C = 4A
  = 3V Max @ I_C = 8A
- Monolithic Construction with Built–In Base–Emitter Shunt Resistors

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO} 80V
Collector–Base Voltage, V_{CB} 80V
Emitter–Base Voltage, V_{EB} 5V
Collector Current, I_C
  Continuous 8A
  Peak 16A
Base Current, I_B 120mA
Total Power Dissipation (T_C = +25°C), P_D 100W
  Derate Above 25°C . . . . . 0.571W/°C
Operating Junction Temperature Range, T_J . . . . . –65° to +200°C
Storage Temperature Range, T_{stg} . . . . . –65° to +200°C
Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 1.78°C/W

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter SustainingVoltage	$V_{CEO(sus)}$	I_C = 100mA, I_B = 0, Note 1	80	–	–	V
Collector Cutoff Current	I_{CEO}	V_{CE} = 40V, I_E = 0	–	–	0.5	mA
	I_{CEX}	V_{CE} = 80V, $V_{BE(off)}$ = 1.5V	–	–	0.5	mA
		V_{CE} = 80V, $V_{BE(off)}$ = 1.5V, T_A = +150°C	–	–	5.0	mA
Emitter Cutoff Current	I_{EBO}	V_{BE} = 5V, I_C = 0	–	–	2.0	mA

Note 1. Pulse Test: Pulse Width = 300µs, Duty Cycle = 2%

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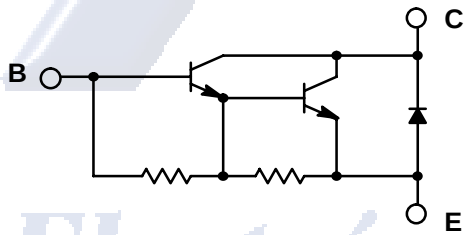
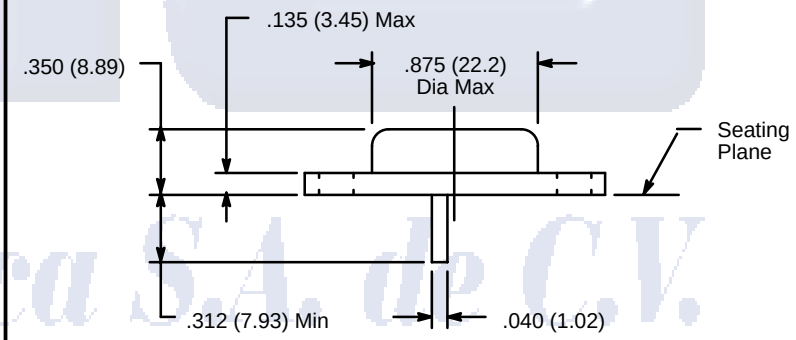
Electrical Characteristics (Cont'd): (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
ON Characteristics (Note 1)						
DC Current Gain	h_{FE}	V_{CE} = 3V, I_C = 4A	750	–	18000	
		V_{CE} = 3V, I_C = 8A	100	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 4A, I_B = 16mA	–	–	2.0	V
		I_C = 8A, I_B = 80mA	–	–	3.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 8A, I_B = 80mA	–	–	4.0	V
Base–Emitter ON Voltage	$V_{BE(on)}$	V_{CE} = 3V, I_C = 4A	–	–	2.8	V
Dynamic Characteristics						
Small–Signal Current Gain	h_{fe}	V_{CE} = 3V, I_C = 3A, f = 1kHz	300	–	–	
Magnitude of Common Emitter Small–Signal Short–Circuit Forward Current Transfer Ratio	$\|h_{fe}\|$	V_{CE} = 3V, I_C = 3A, f = 1MHz	4.0	–	–	MHz
Output Capacitance NTE243	C_{ob}	V_{CB} = 10V, I_E = 0, f = 0.1MHz	–	–	200	pF
NTE244			–	–	300	pF

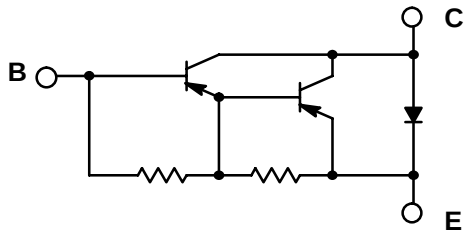
Note 1. Pulse Test: Pulse Width = 300µs, Duty Cycle = 2%

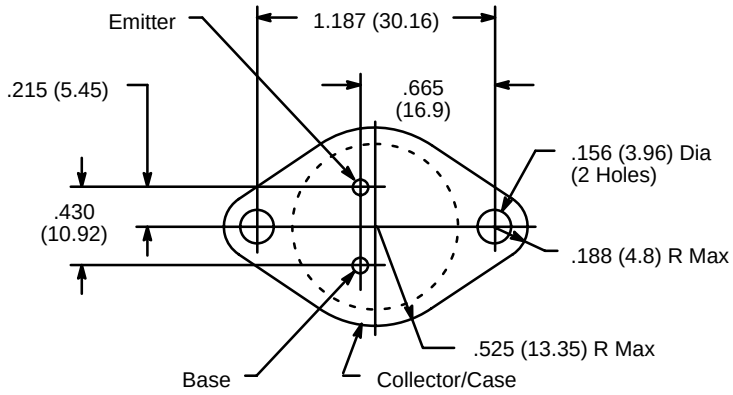
NTE243





NTE244





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